Stephane Calvez

List of Publications by Year in Descending Order

101 papers	1,586 citations	21 h-index	36 g-index
153 ext. papers	1,868 ext. citations	2.4 avg, IF	3.89 L-index

#	Paper	IF	Citations
101	Cavity resonator-integrated guided-mode resonance filters with on-chip electro- and thermo-optic tuning. *Optics Express*, **2022**, 30, 16669	3.3	
100	Dark mode-in-the-box for enhanced second-harmonic generation in corrugated waveguides. *Optics Express*, **2021**, 29, 40981	3.3	1
99	Engineering the anisotropy of AlAs wet oxidation using silicon implantation. *Optical Materials Express*, **2021**, 11, 3600	2.6	
98	Selective wet oxidation of AlAsSb alloys on GaAs. *AIP Advances*, **2021**, 11, 125010	1.5	
97	3.3 μm interband-cascade resonant-cavity light-emitting diode with narrow spectral emission linewidth. *Semiconductor Science and Technology*, **2020**, 35, 125029	1.8	1
96	Modeling the Lateral Wet Oxidation of AlxGa1−xAs into Arbitrary Mesa Geometries. *Physical Review Applied*, **2019**, 11,	4.3	2
95	Interband cascade Lasers with AlGaAsSb cladding layers emitting at 3.3 μm. *Optics Express*, **2019**, 27, 31425-31434	3.3	6
94	Numerical studies on Kerr comb generation in Si3N4 resonators with frequency dependent access coupler properties **2019**,		1
93	Numerical study on Kerr frequency comb generation in Si3N4 microresonators with frequency-dependent access coupler properties. *Journal of the Optical Society of America B: Optical Physics*, **2019**, 36, 2896	1.7	
92	Second-harmonic-generation enhancement in cavity resonator integrated grating filters. *Optics Letters*, **2019**, 44, 5198-5201	3	4
91	Thermally-tunable cavity resonator-integrated guided-mode resonance filters. *OSA Continuum*, **2019**, 2, 3204	1.4	1
90	High frequency operation of an integrated electro-absorption modulator onto a vertical-cavity surface-emitting laser. *JPhys Photonics*, **2019**, 1, 02LT01	2.5	3
89	Anisotropic lateral oxidation of Al-III-V semiconductors: inverse problem and circular aperture fabrication. *Semiconductor Science and Technology*, **2019**, 34, 015014	1.8	3
88	Vertical electro-absorption modulator design and its integration in a VCSEL. *Journal Physics D: Applied Physics*, **2018**, 51, 145101	3	4
87	. *IEEE Journal of Quantum Electronics*, **2018**, 54, 1-8	2	
86	Modelling anisotropic lateral oxidation from circular mesas. *Optical Materials Express*, **2018**, 8, 1762	2.6	7
85	Anisotropy in the wet thermal oxidation of AlGaAs: influence of process parameters. *Optical Materials Express*, **2018**, 8, 1788	2.6	7

84	Highly-resonant two-polarization transmission guided-mode resonance filter. *AIP Advances*, **2018**, 8, 115228	1.5	7
83	Coupled mode analysis of micro-disk resonators with an asymmetric-index-profile coupling region **2017**,		3
82	Oxide-confined VCSELs fabricated with a simple self-aligned process flow. *Semiconductor Science and Technology*, **2017**, 32, 125004	1.8	1
81	Low-loss buried AlGaAs/AlOx waveguides using a quasi-planar process. *Optics Express*, **2017**, 25, 19275-19280	3.3	2
80	Achromatic critically coupled racetrack resonators. *Journal of the Optical Society of America B: Optical Physics*, **2017**, 34, 2343	1.7	3
79	Vertically Coupled Microdisk Resonators Using AlGaAs/AlOx Technology. *IEEE Photonics Technology Letters*, **2015**, 27, 982-985	2.2	10
78	Photoluminescence from InGaAs/GaAs quantum well regrown on a buried patterned oxidized AlAs layer. *Applied Physics Letters*, **2014**, 104, 061912	3.4	2
77	Thermal Management of Lasers and LEDs Using Diamond **2013**, 353-384		1
76	Quantum Confinement Stark Effect of Different Gainnas Quantum Well Structures. *Advanced Materials Research*, **2013**, 773, 622-627	0.5	
75	Power-scaling properties of apertured microchip vertical external-cavity surface-emitting lasers. *Electronics Letters*, **2013**, 49, 146-148	1.1	
74	Semiconductor disk lasers (VECSELs) **2013**, 341-393		2
73	Thermal Management of Near-Infrared Semiconductor Disk Lasers With AlGaAs Mirrors and Lattice (Mis)Matched Active Regions. *IEEE Journal of Quantum Electronics*, **2012**, 48, 345-352	2	13
72	Wavelength-stabilised external-cavity laser diode using cavity resonator integrated guided mode filter. *Electronics Letters*, **2012**, 48, 1619-1621	1.1	16
71	Optical trapping with "on-demand" two-photon luminescence using Cr:LiSAF laser with optically addressed saturable Bragg reflector. *Optics Express*, **2012**, 20, 7066-70	3.3	7
70	Electrically-controlled rapid femtosecond pulse duration switching and continuous picosecond pulse duration tuning in an ultrafast Cr4+:forsterite laser. *Optics Express*, **2012**, 20, 18138-44	3.3	6
69	Large cross-section edge-coupled diamond waveguides. *Diamond and Related Materials*, **2011**, 20, 564-567	3.5	16
68	Broadly tunable femtosecond mode-locking in a Tm:KYW laser near 2 μm. *Optics Express*, **2011**, 19, 9995-10000	3.5	58
67	Passively Q-switched Pr:YLF laser **2011**,		7

66	Diamond Raman Waveguide Lasers: Completely Analytical Design Optimization Incorporating Scattering Losses. *IEEE Journal of Quantum Electronics*, **2011**, 47, 1069-1077	2	15
65	GaInNAs(Sb) for solid-state laser engineering **2011**,		1
64	GaN directional couplers for integrated quantum photonics. *Applied Physics Letters*, **2011**, 99, 161119	3.4	46
63	650MHz -prf-femtosecond Cr4+:forsterite laser with dispersion-compensating GaInNAs SESAM **2011**,		1
62	Thermal Management, Structure Design, and Integration Considerations for VECSELs **2010**, 73-117		8
61	Passive Mode-Locking of a Ti : Sapphire Laser by InGaP Quantum-Dot Saturable Absorber. *IEEE Photonics Technology Letters*, **2010**, 22, 209-211	2.2	15
60	Cavity-dumping of a semiconductor disk laser for the generation of wavelength-tunable micro-Joule nanosecond pulses. *Optics Express*, **2010**, 18, 11933-41	3.3	12
59	Femtosecond mode-locked Tm(3+) and Tm(3+)-Ho(3+) doped 2 μm glass lasers. *Optics Express*, **2010**, 18, 22090-8	3.3	51
58	Femtosecond pulse operation of a Tm,Ho-codoped crystalline laser near 2 microm. *Optics Letters*, **2010**, 35, 172-4	3	57
57	Femtosecond (191 fs) NaY(WO4)2 Tm,Ho-codoped laser at 2060 nm. *Optics Letters*, **2010**, 35, 3027-9	3	69
56	Optically Pumped Saturable Bragg Reflectors: Nonlinear Spectroscopy and Application in Ultrafast Lasers. *IEEE Journal of Quantum Electronics*, **2010**, 46, 1650-1655	2	6
55	1.55-μm tunable doped-fiber vertical-cavity surface emitting laser **2009**,		1
54	Semiconductor disk lasers for the generation of visible and ultraviolet radiation. *Laser and Photonics Reviews*, **2009**, 3, 407-434	8.3	118
53	Passive mode locking of a Tm,Ho:KY(WO4)2 laser around 2 microm. *Optics Letters*, **2009**, 34, 2587-9	3	49
52	Optically-pumped saturable absorber for fast switching between continuous-wave and passively mode-locked regimes of a Nd:YVO4 laser. *Optics Express*, **2009**, 17, 5373-8	3.3	7
51	InP/AlGaInP quantum dot semiconductor disk lasers for CW TEM00 emission at 716 - 755 nm. *Optics Express*, **2009**, 17, 21782-7	3.3	34
50	Thermal lens study in diode pumped Ng- and Np-cut Nd:KGd(WO4)2 laser crystals. *Optics Express*, **2009**, 17, 23536-43	3.3	40
49	Power-Scaling of Diamond Microlensed Microchip Semiconductor Disk Lasers. *IEEE Photonics Technology Letters*, **2009**, 21, 152-154	2.2	7

48	GaInNAs semiconductor disk lasers as pump sources for Tm3+(,Ho3+)-doped glass, crystal and fibre lasers **2009**,		4
47	Femtosecond pulse generation around 1500 nm using a GaInNAsSb SESAM. *Optics Express*, **2008**, 16, 18739-44	3.3	8
46	Continuous Tuning and Efficient Intracavity Second-Harmonic Generation in a Semiconductor Disk Laser With an Intracavity Diamond Heatspreader. *IEEE Journal of Quantum Electronics*, **2008**, 44, 216-225	2	29
45	Array-Format Microchip Semiconductor Disk Lasers. *IEEE Journal of Quantum Electronics*, **2008**, 44, 1096-1103	2	6
44	1213nm semiconductor disk laser pumping of a Tm3+-doped tellurite glass laser **2008**,		1
43	Short-wavelength GaInNAs/GaAs semiconductor disk lasers. *Electronics Letters*, **2008**, 44, 1069	1.1	10
42	Quantum-well intermixing influence on GaInNAs/GaAs quantum-well laser gain: theoretical study. *Semiconductor Science and Technology*, **2008**, 23, 095010	1.8	8
41	Characterisation of an InAs quantum dot semiconductor disk laser **2008**,		1
40	Comparison of thermal management techniques for semiconductor disk lasers **2008**,		9
39	GaInNAs(Sb) surface normal devices. *Physica Status Solidi (A) Applications and Materials Science*, **2008**, 205, 85-92	1.6	7
38	Tunable red laser emission by intra-cavity frequency-doubling of a GaInNAs VECSEL **2007**,		1
37	High performance 2.2 μm optically-pumped vertical external-cavity surface-emitting laser. *Journal of Modern Optics*, **2007**, 54, 1677-1683	1.1	4
36	Thermal management in disc lasers: doped-dielectric and semiconductor laser gain media in thin-disc and microchip formats. *Journal of Modern Optics*, **2007**, 54, 1669-1676	1.1	6
35	Tunable single-mode fiber-VCSEL using an intracavity polymer microlens. *Optics Letters*, **2007**, 32, 2831-3	3	8
34	Microlensed microchip VECSEL. *Optics Express*, **2007**, 15, 9341-6	3.3	17
33	Stabilization of a semiconductor disk laser using an intra-cavity high reflectivity grating. *Optics Express*, **2007**, 15, 16520-6	3.3	12
32	C-band emission from GaInNAsSb VCSEL on GaAs. *Electronics Letters*, **2006**, 42, 29	1.1	11
31	Corrections to "Thermal Management in Vertical-External-Cavity Surface-Emitting Lasers: Finite-Element Analysis of a Heatspreader Approach" *IEEE Journal of Quantum Electronics*, **2006**, 42, 85-85	2	1

30	Spectral narrowing and locking of a vertical-external-cavity surface-emitting laser using an intracavity volume Bragg grating. *IEEE Photonics Technology Letters*, **2006**, 18, 1786-1788	2.2	16
29	Slow-light in a vertical-cavity semiconductor optical amplifier. *Optics Express*, **2006**, 14, 6858-63	3.3	13
28	Intracavity diamond heatspreaders in lasers: the effects of birefringence. *Optics Express*, **2006**, 14, 9250-60	3.3	32
27	High-power vertical external-cavity surface-emitting lasers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 380-385		6
26	Thermal lensing, thermal management and transverse mode control in microchip VECSELs. *Applied Physics B: Lasers and Optics*, **2006**, 83, 189-194	1.9	21
25	Thermal management in vertical-external-cavity surface-emitting lasers: finite-element analysis of a heatspreader approach. *IEEE Journal of Quantum Electronics*, **2005**, 41, 148-155	2	80
24	Performance comparison of GaInNAs vertical-cavity semiconductor optical amplifiers. *IEEE Journal of Quantum Electronics*, **2005**, 41, 642-649	2	3
23	High power CW red VECSEL with linearly polarized TEM00 output beam. *Optics Express*, **2005**, 13, 77-81	3.3	99
22	Red microchip VECSEL array. *Optics Express*, **2005**, 13, 7209-14	3.3	17
21	Low-loss GaInNAs saturable Bragg reflector for mode-locking of a femtosecond Cr/sup 4+/ : forsterite-laser. *IEEE Photonics Technology Letters*, **2005**, 17, 2292-2294	2.2	8
20	Index and gain dynamics of optically pumped GaInNAs vertical-cavity semiconductor optical amplifiers. *Applied Physics Letters*, **2005**, 87, 231115	3.4	5
19	Influence of composition diffusion on the band structures of InGaNAs□GaAs quantum wells investigated by the band-anticrossing model. *Applied Physics Letters*, **2005**, 87, 231112	3.4	7
18	Photoluminescence characteristics of 1.5-□m Ga1-xInxNyAs1-y/GaAs structures grown by molecular beam epitaxy. *Applied Physics A: Materials Science and Processing*, **2005**, 80, 9-12	2.6	
17	Fiber-tunable dilute-nitride VCSEL. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2005**, 2, 3895-3898		5
16	High Power, Continuous Wave Operation of a Vertical External Cavity Surface Emitting Laser at 674nm **2005**,		1
15	0.6 W CW GaInNAs vertical external-cavity surface emitting laser operating at 1.32 [micro sign]m. *Electronics Letters*, **2004**, 40, 30	1.1	101
14	Diamond-microchip GaInNAs vertical external-cavity surface-emitting laser operating CW at 1315 nm. *Electronics Letters*, **2004**, 40, 935	1.1	28
13	1.3-□m GaInNAs surface-normal devices. *IEE Proceedings: Optoelectronics*, **2004**, 151, 442-446		3

12	GaInNAs/GaAs Bragg-mirror-based structures for novel 1.3□m device applications. *Journal of Crystal Growth*, **2004**, 268, 457-465	1.6	22
11	Long-wavelength monolithic GaInNAs vertical-cavity optical amplifiers. *IEEE Journal of Quantum Electronics*, **2004**, 40, 878-883	2	14
10	Resonant wavelength control of a 1.3 □m microcavity by intracavity steam oxidation. *Semiconductor Science and Technology*, **2003**, 18, L12-L15	1.8	1
9	Microchip vertical external cavity surface emitting lasers. *Electronics Letters*, **2003**, 39, 1324	1.1	34
8	Microreflectivity studies of wavelength control in oxidised AlGaAs microcavities. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 102, 317-322	3.1	
7	0.5-W single transverse-mode operation of an 850-nm diode-pumped surface-emitting semiconductor laser. *IEEE Photonics Technology Letters*, **2003**, 15, 894-896	2.2	91
6	1.3 m GaInNAs optically-pumped vertical cavity semiconductor optical amplifier. *Electronics Letters*, **2003**, 39, 100	1.1	28
5	Low-loss 1.3-microm GaInNAs saturable Bragg reflector for high-power picosecond neodymium lasers. *Optics Letters*, **2002**, 27, 2124-6	3	46
4	Optimization of an optically pumped 1.3-□m GaInNAs vertical-cavity surface-emitting laser. *IEEE Photonics Technology Letters*, **2002**, 14, 131-133	2.2	23
3	1.3 /spl mu/m GaInNAs monolithic vertical-cavity semiconductor optical amplifier		2
2	A diamond-microchip GaInNAs VECSEL operating at 1315 nm		1
1	Amplification and laser action in diode-pumped 1.3 /spl mu/m GaInNAs vertical-cavity structures		1